

N-channel 100 V, 120 mΩ logic level MOSFET in LFPAK33 19 September 2016 Product data sheet

19 September 201

### 1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V<sub>GS(th)</sub> rating of greater than 0.5 V at 175 °C

### 3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	11.5	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	44	W
Static charact	eristics	·					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>		-	100	120	mΩ
Dynamic characteristics							
Q <sub>GD</sub>	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 13}}{13}; \frac{\text{Fig. 14}}{14}$		-	3.9	-	nC

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source	$\bigcirc$	G L F 4
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

# 6. Ordering information

Table 3. Ordering information							
Type number	Package	ige					
	Name	Description	Version				
BUK9M120-100E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210				

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9M120-100E	912010

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	100	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	10	V
		Pulsed; T <sub>j</sub> ≤ 175 °C	[1][2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	44	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	11.5	А
		V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	8.1	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 3		-	46	А

BUK9M120-100E

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	11.5	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	46	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 11.5 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3][4]	-	13.2	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm. Significantly longer life times are achieved by lowering  $\rm T_{j}$  and or  $\rm V_{GS}$ [1]
- [2]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]
- Refer to application note AN10273 for further information. [4]

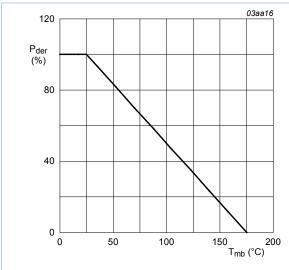


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

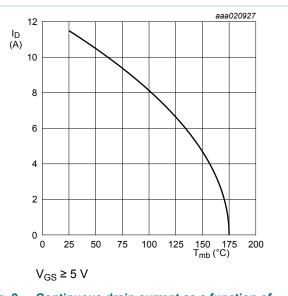
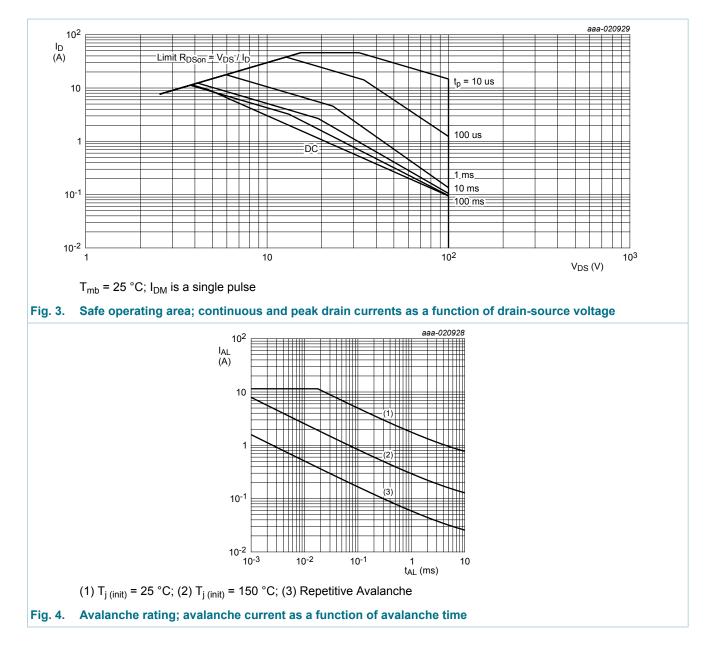


Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 115A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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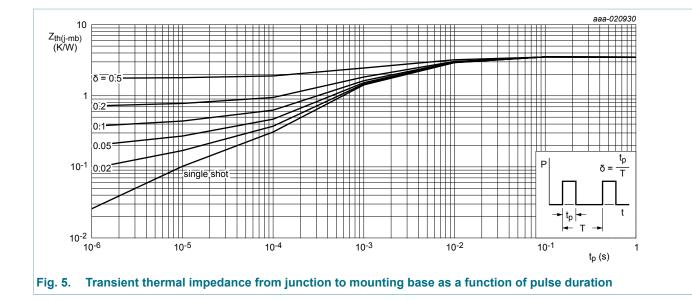


### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	2.77	3.4	K/W

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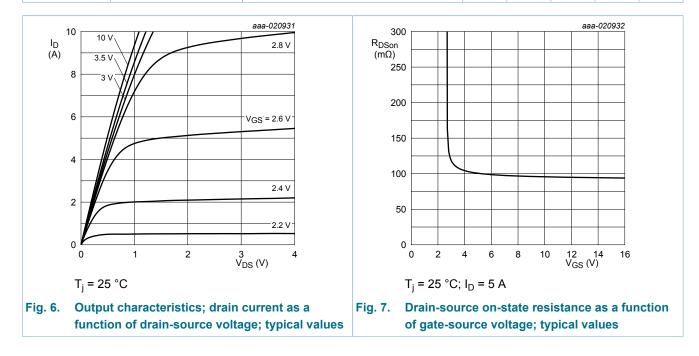
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	l				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
breakdown voltage	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
V <sub>GS(th)</sub> gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.05	V	
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 10	-	-	2.45	V
	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10	0.5	-	-	V	
I <sub>DSS</sub> drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.01	1	μA	
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	100	120	mΩ
	resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	96	119	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; <u>Fig. 12</u>	-	-	340	mΩ
Dynamic ch	naracteristics	· · ·				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 5 V;	-	8.8	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	1.7	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	3.9	-	nC

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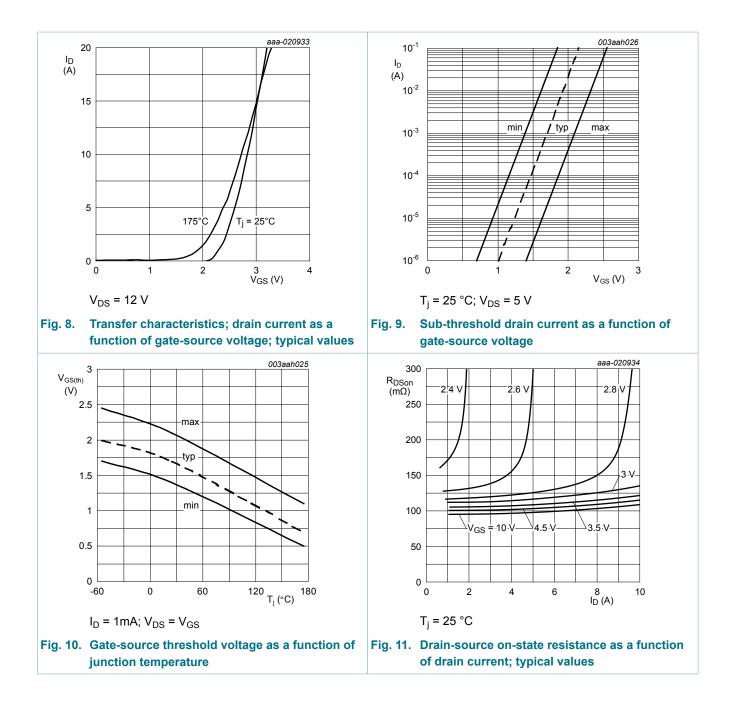
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;$ T = 25 °C; Fig. 15		-	663	882	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	52	63	pF
C <sub>rss</sub>	reverse transfer capacitance			-	35	48	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 80 V; R <sub>L</sub> = 15 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C		-	6.1	-	ns
t <sub>r</sub>	rise time			-	9.1	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	14.1	-	ns
t <sub>f</sub>	fall time	-		-	8.3	-	ns
Source-dra	ain diode	1	1	1			
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 5 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>		-	0.84	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 5 \text{ A; } dI_{S}/dt = -100 \text{ A}/\mu\text{s; } V_{GS} = 0 \text{ V;}$ $V_{DS} = 25 \text{ V; } T_{j} = 25 \text{ °C}$		-	27.4	-	ns
Q <sub>r</sub>	recovered charge			-	35.5	-	nC



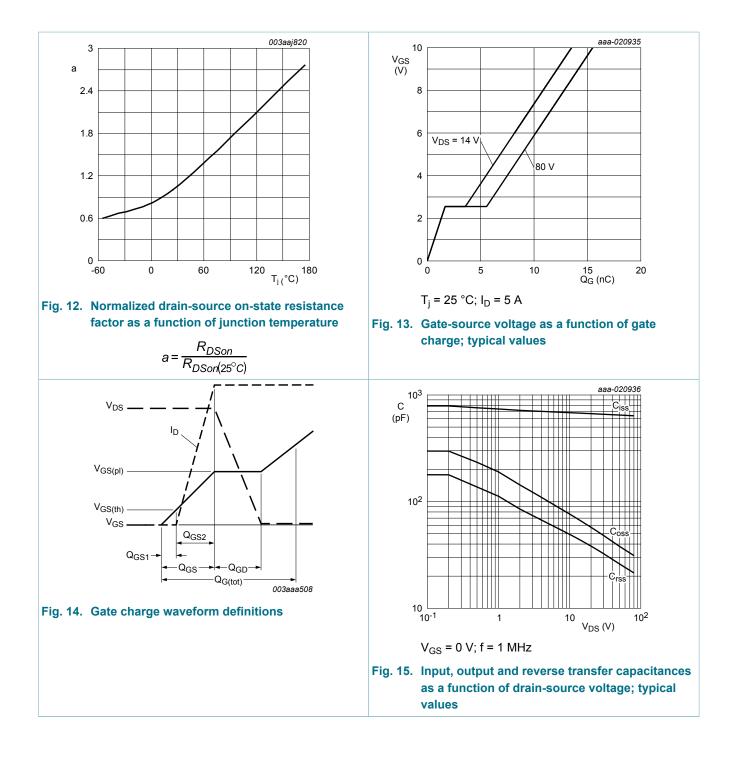
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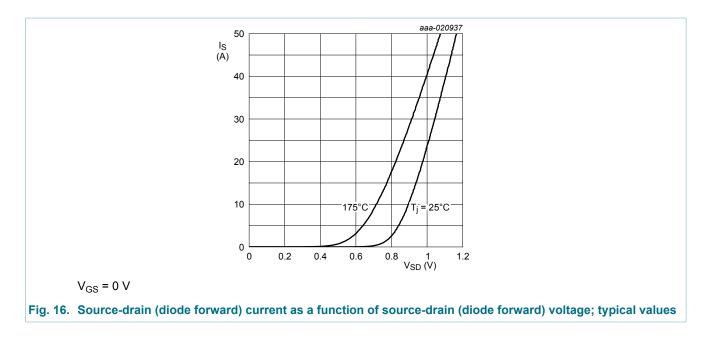
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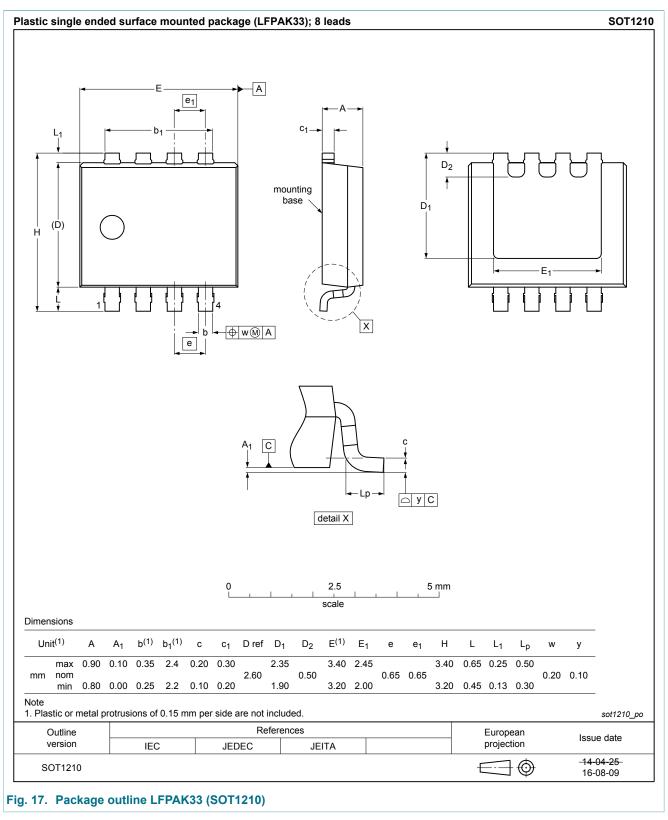


# **11. Application information**

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

N-channel 100 V, 120 mΩ logic level MOSFET in LFPAK33

### 12. Package outline



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Product data sheet

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#### N-channel 100 V, 120 mΩ logic level MOSFET in LFPAK33

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